

Trench gate field-stop IGBT, V series 600 V, 30 A very high speed

Datasheet - production data

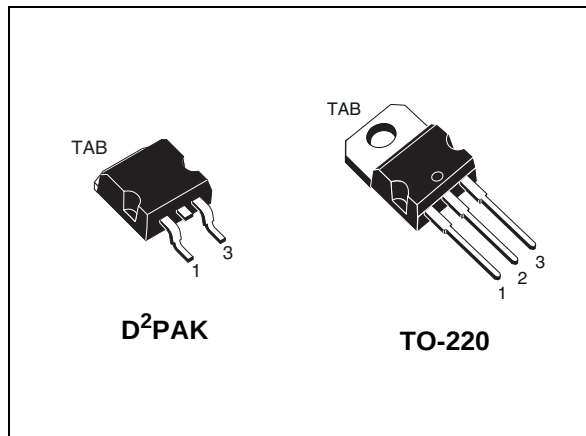
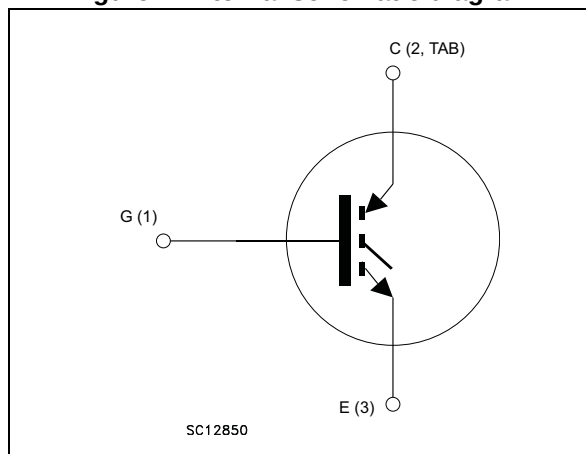


Figure 1. Internal schematic diagram



Features

- Maximum junction temperature: $T_J = 175\text{ °C}$
- Tail-less switching off
- $V_{CE(sat)} = 1.85\text{ V (typ.) @ } I_C = 30\text{ A}$
- Tight parameters distribution
- Safe paralleling
- Low thermal resistance

Applications

- Photovoltaic inverters
- Uninterruptible power supply
- Welding
- Power factor correction
- Very high frequency converters

Description

This device is an IGBT developed using an advanced proprietary trench gate field stop structure. The device is part of the V series of IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of very high frequency converters. Furthermore, a positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STGB30V60F	GB30V60F	D²PAK	Tape and reel
STGP30V60F	GP30V60F	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$)	600	V
I_C	Continuous collector current at $T_C = 25\text{ °C}$	60	A
I_C	Continuous collector current at $T_C = 100\text{ °C}$	30	A
$I_{CP}^{(1)}$	Pulsed collector current	120	A
V_{GE}	Gate-emitter voltage	± 20	V
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	260	W
T_{STG}	Storage temperature range	- 55 to 150	°C
T_J	Operating junction temperature	- 55 to 175	°C

1. Pulse width limited by maximum junction temperature.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case	0.58	°C/W
R_{thJA}	Thermal resistance junction-ambient	62.5	°C/W

2 Electrical characteristics

$T_J = 25\text{ °C}$ unless otherwise specified.

Table 4. Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 2\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 30\text{ A}$		1.85	2.3	V
		$V_{GE} = 15\text{ V}$, $I_C = 30\text{ A}$ $T_J = 125\text{ °C}$		2.15		
		$V_{GE} = 15\text{ V}$, $I_C = 30\text{ A}$ $T_J = 175\text{ °C}$		2.35		
V_F	Forward on-voltage	$I_F = 30\text{ A}$		2	2.6	V
		$I_F = 30\text{ A}$, $T_J = 125\text{ °C}$		1.7		V
		$I_F = 30\text{ A}$, $T_J = 175\text{ °C}$		1.6		V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$	5	6	7	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 600\text{ V}$			25	μA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{ V}$			250	nA

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$	-	3750	-	pF
C_{oes}	Output capacitance		-	120	-	pF
C_{res}	Reverse transfer capacitance		-	77	-	pF
Q_g	Total gate charge	$V_{CC} = 480\text{ V}$, $I_C = 30\text{ A}$, $V_{GE} = 15\text{ V}$, see Figure 22	-	163	-	nC
Q_{ge}	Gate-emitter charge		-	28	-	nC
Q_{gc}	Gate-collector charge		-	72	-	nC

Table 6. IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 30\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, see Figure 21	-	45	-	ns
t_r	Current rise time		-	16	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1500	-	A/ μ s
$t_{d(off)}$	Turn-off delay time		-	189	-	ns
t_f	Current fall time		-	19	-	ns
$E_{on}^{(1)}$	Turn-on switching losses		-	383	-	μ J
$E_{off}^{(2)}$	Turn-off switching losses		-	233	-	μ J
E_{ts}	Total switching losses		-	616	-	μ J
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 30\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$, see Figure 21	-	42	-	ns
t_r	Current rise time		-	17	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	1337	-	A/ μ s
$t_{d(off)}$	Turn-off delay time		-	193	-	ns
t_f	Current fall time		-	32	-	ns
$E_{on}^{(1)}$	Turn-on switching losses		-	794	-	μ J
$E_{off}^{(2)}$	Turn-off switching losses		-	378	-	μ J
E_{ts}	Total switching losses		-	1172	-	μ J

1. Energy losses include reverse recovery of the external diode. The diode is the same of the copacked STGW30V60DF.

2. Turn-off losses include also the tail of the collector current.

2.1 Electrical characteristics (curves)

Figure 2. Power dissipation vs. case temperature

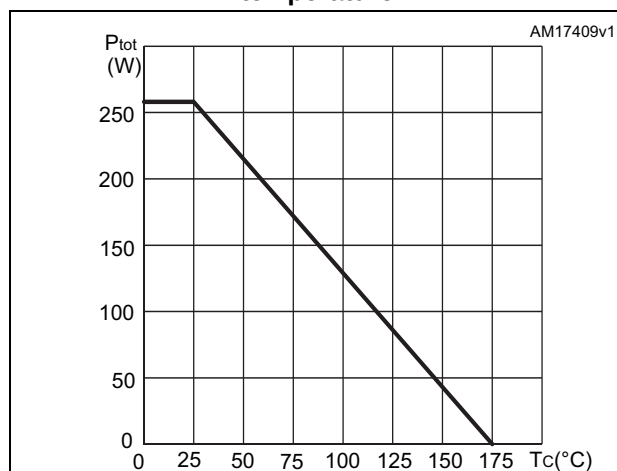


Figure 3. Collector current vs. case temperature

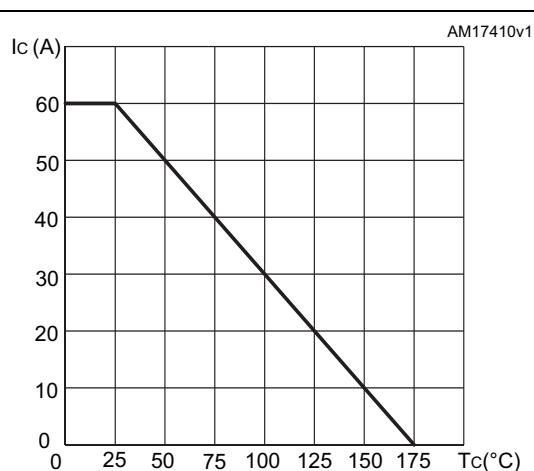


Figure 4. Output characteristics ($T_J=25^\circ\text{C}$)

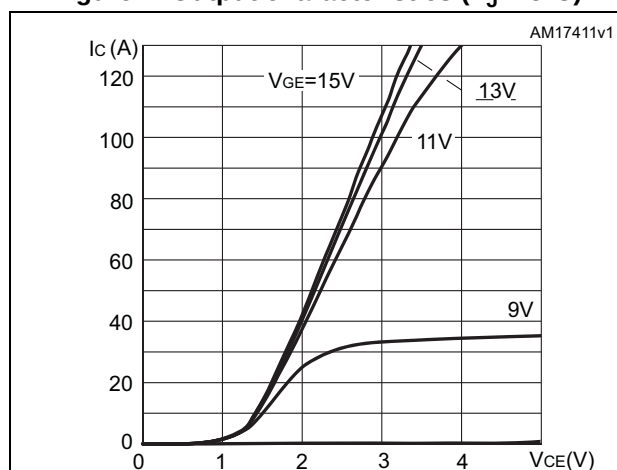


Figure 5. Output characteristics ($T_J=175^\circ\text{C}$)

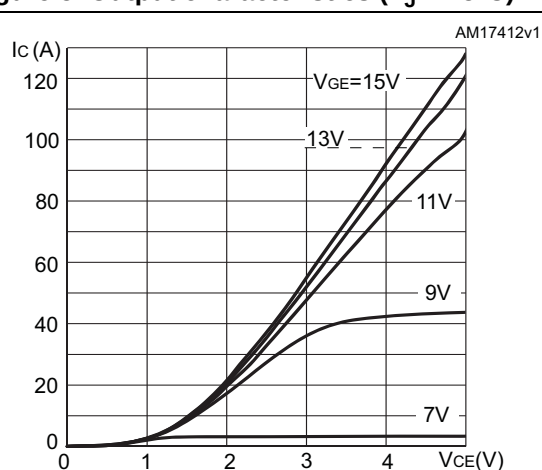


Figure 6. $V_{CE(sat)}$ vs. junction temperature

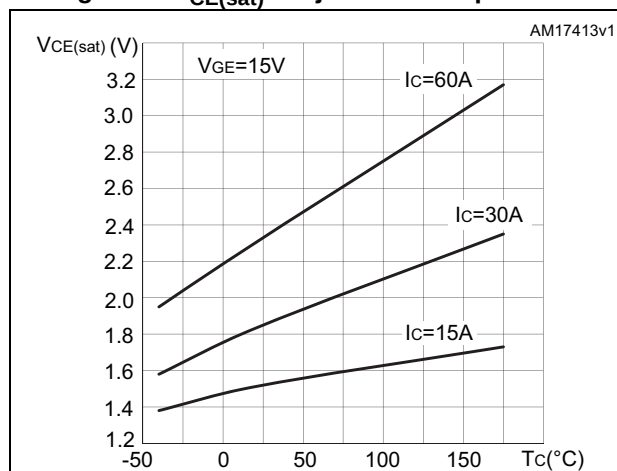


Figure 7. $V_{CE(sat)}$ vs. collector current

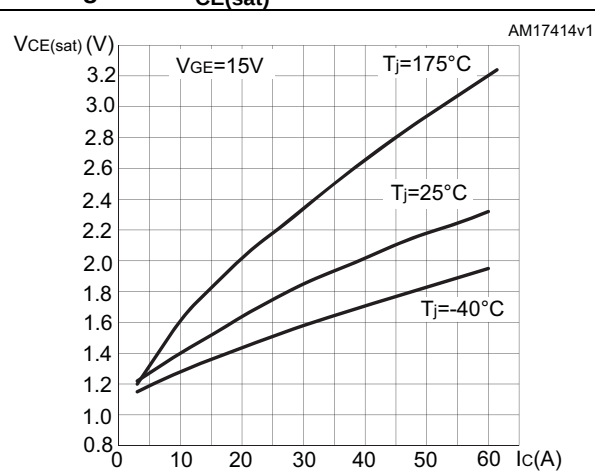


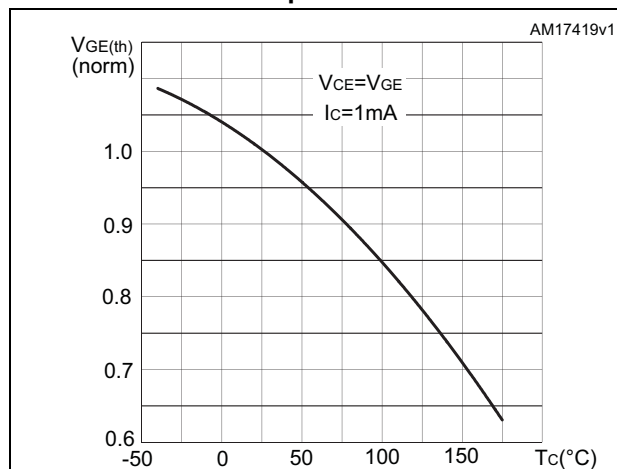
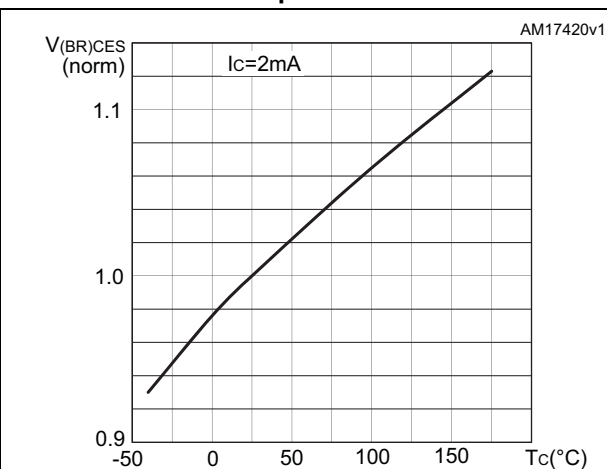
Figure 8. Normalized $V_{GE(th)}$ vs junction temperatureFigure 9. Normalized $V_{(BR)CES}$ vs. junction temperature

Figure 10. Capacitance variations

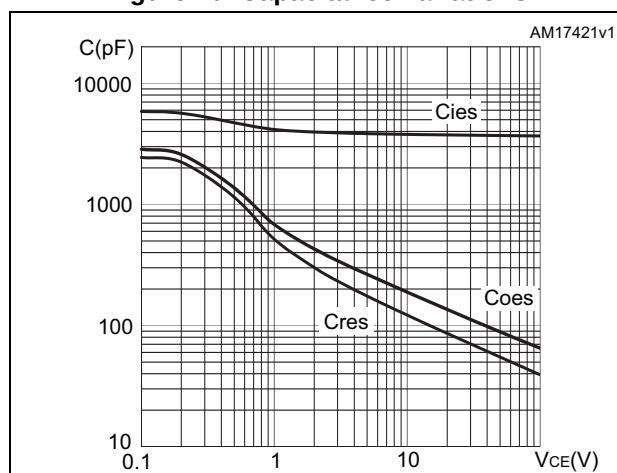


Figure 11. Gate charge vs. gate-emitter voltage

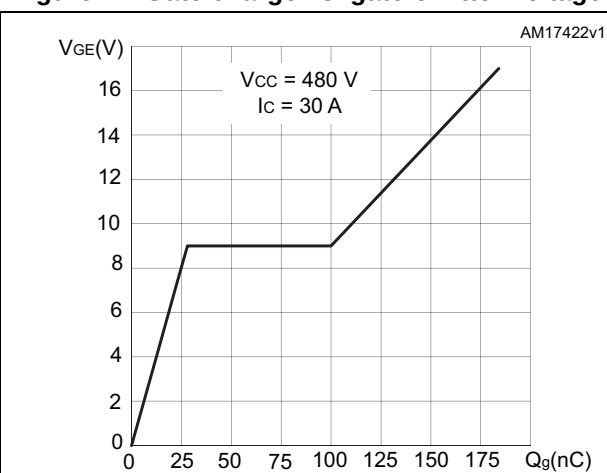


Figure 12. Switching losses vs. collector current

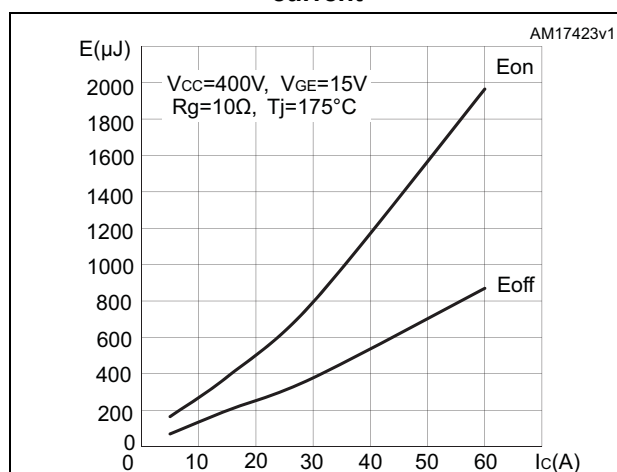


Figure 13. Switching losses vs. gate resistance

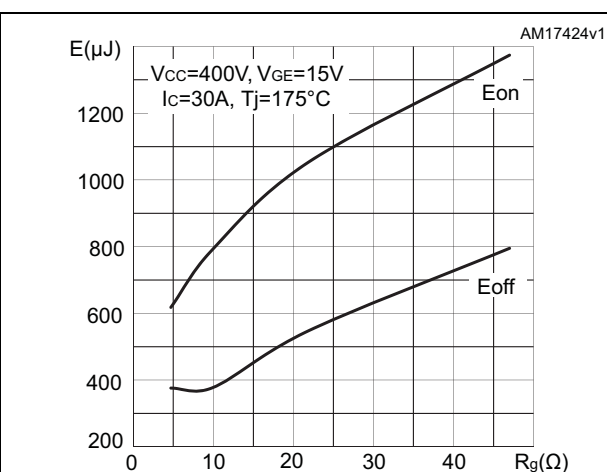


Figure 14. Switching losses vs. junction temperature

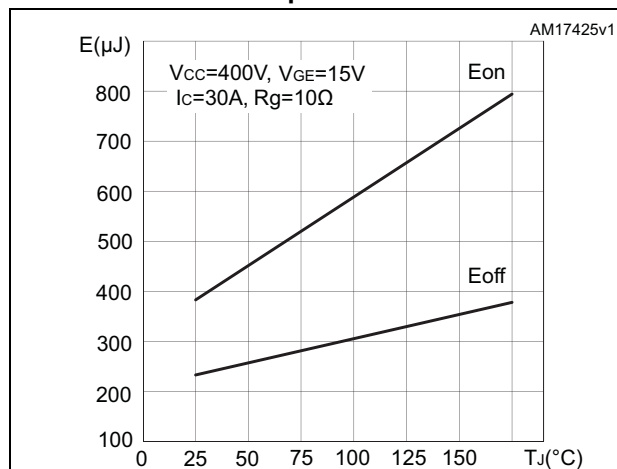


Figure 15. Switching losses vs. collector emitter voltage

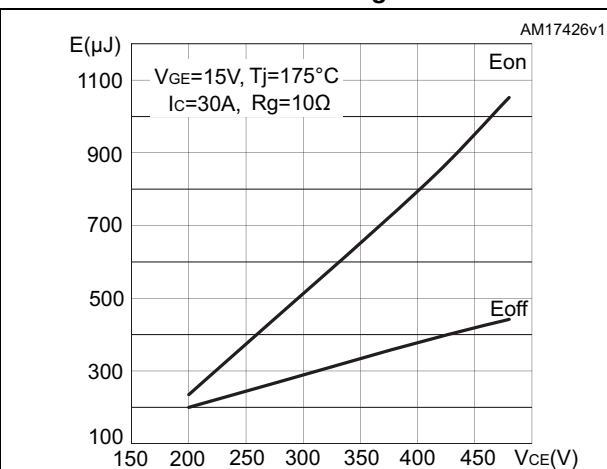


Figure 16. Switching times vs. collector current

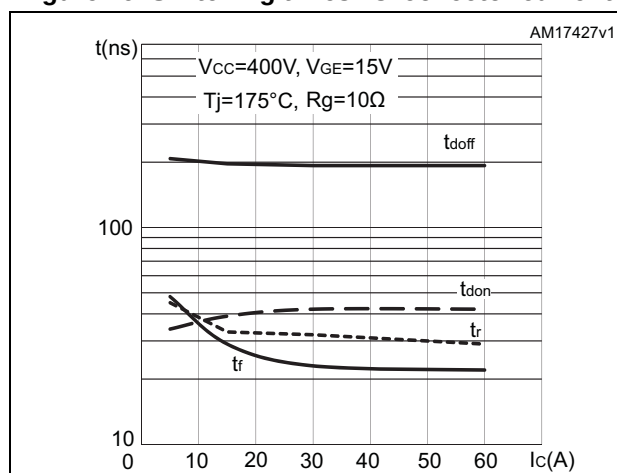


Figure 17. Switching times vs. gate resistance

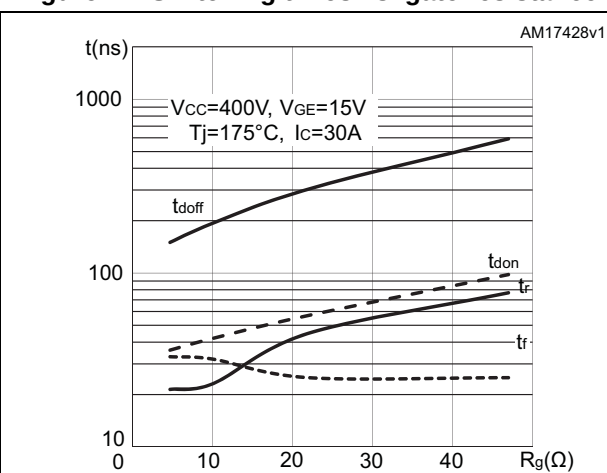


Figure 18. Transfer characteristics

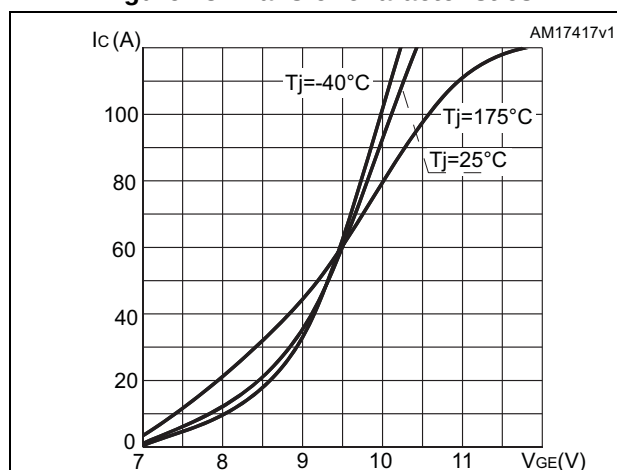


Figure 19. Safe operating area

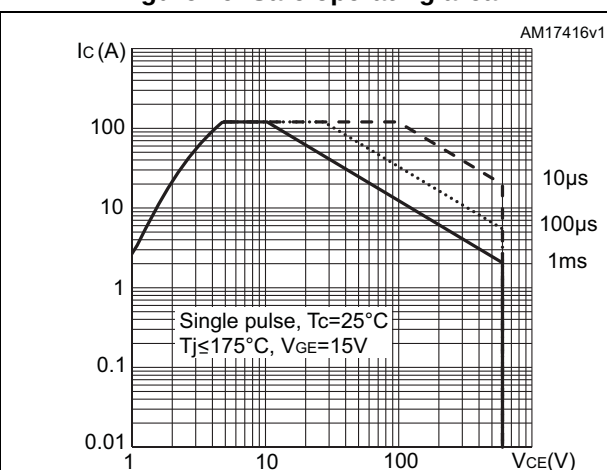
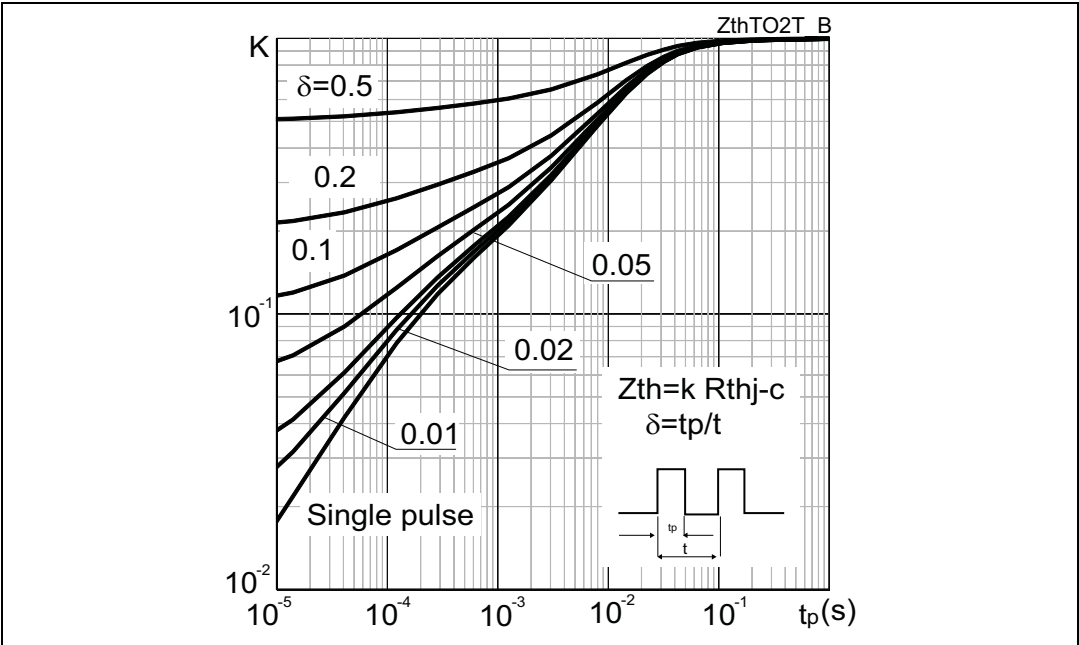
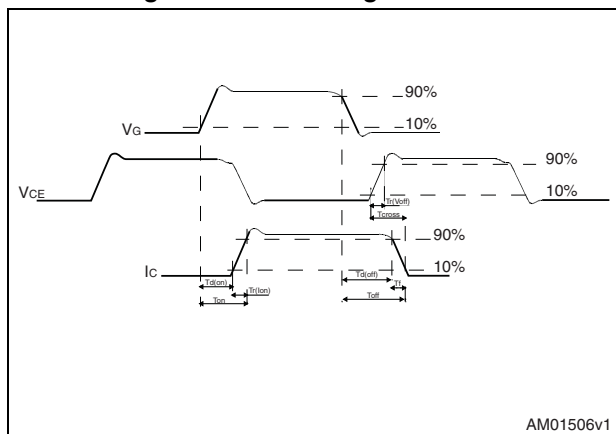
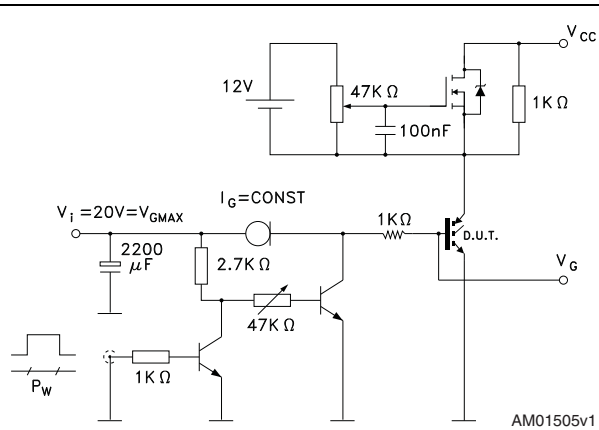
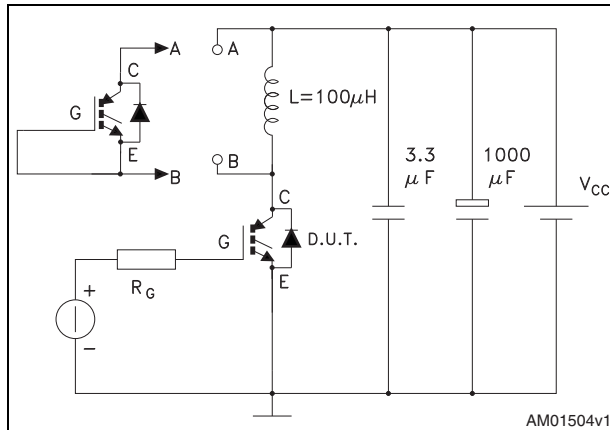


Figure 20. Thermal data





4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 7. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 24. D²PAK (TO-263) drawing

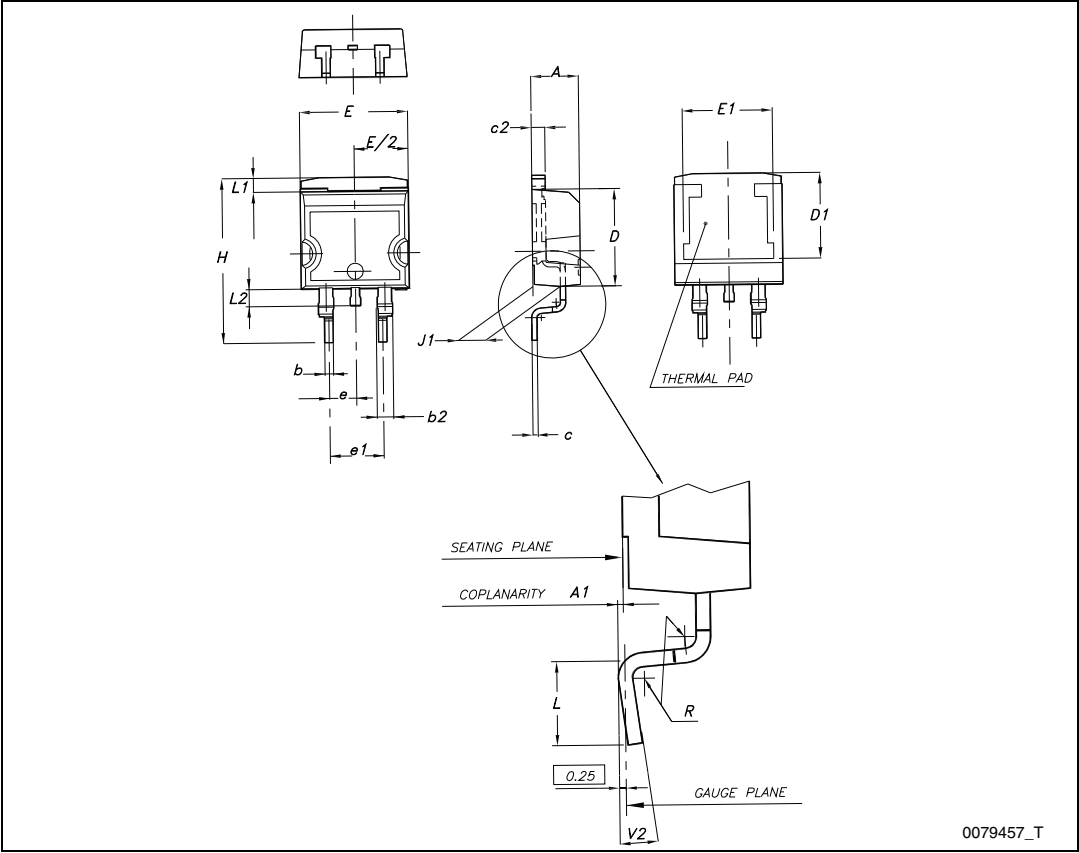
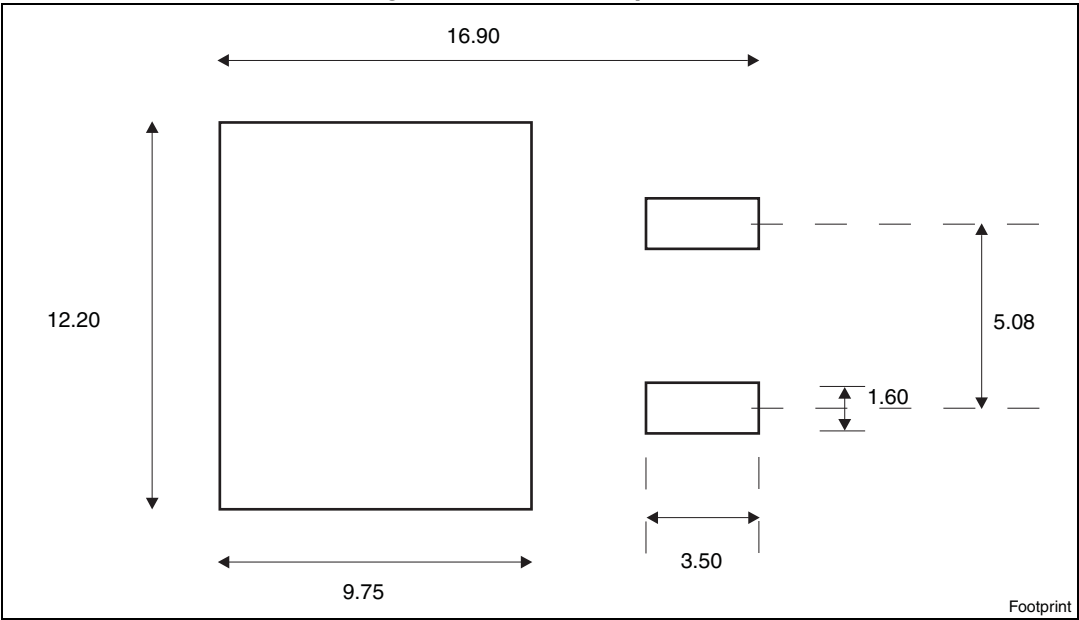
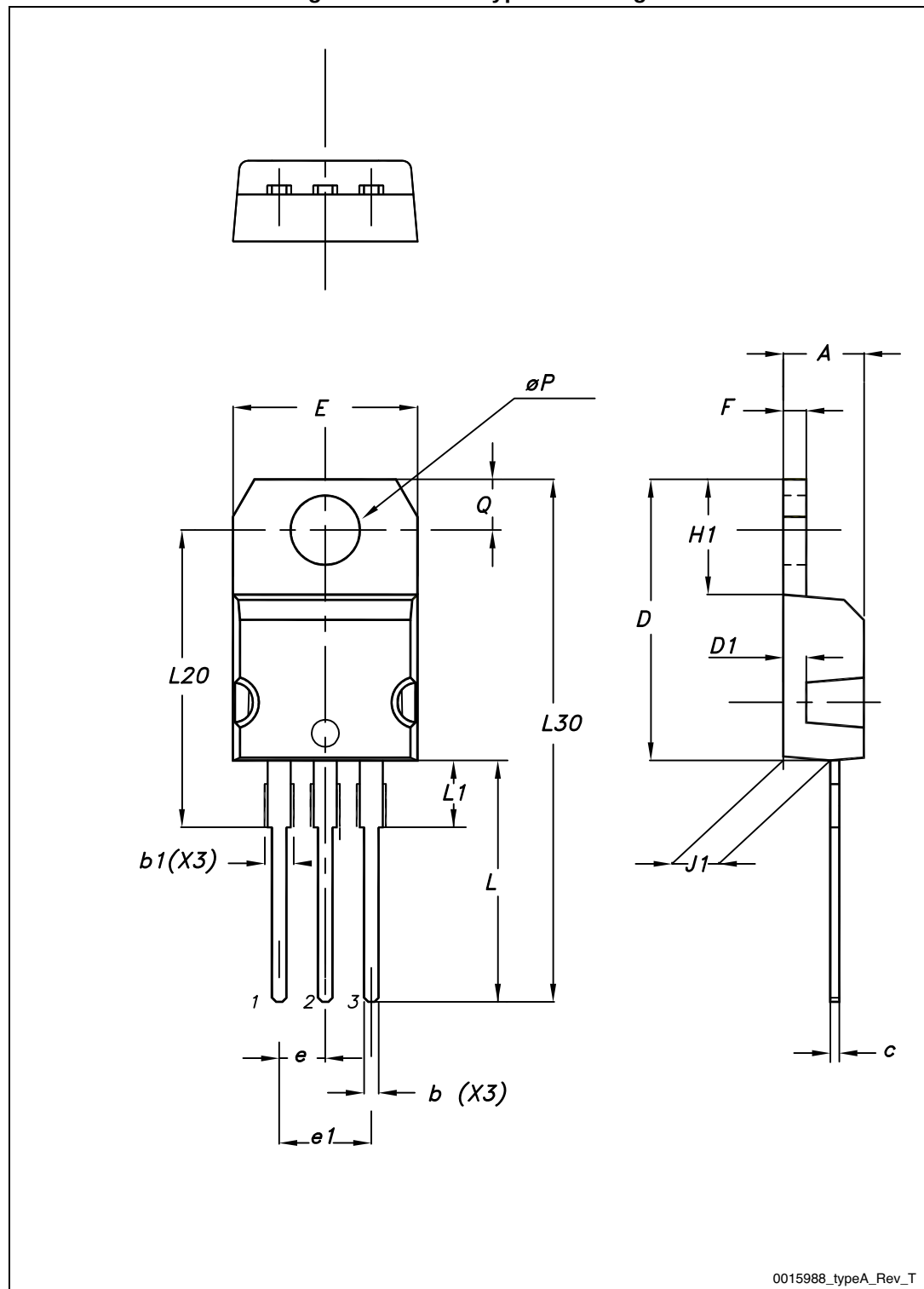


Figure 25. D²PAK footprint^(a)



a. All dimension are in millimeters

Figure 26. TO-220 type A drawing



5 Packaging mechanical data

Table 8. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 27. Tape

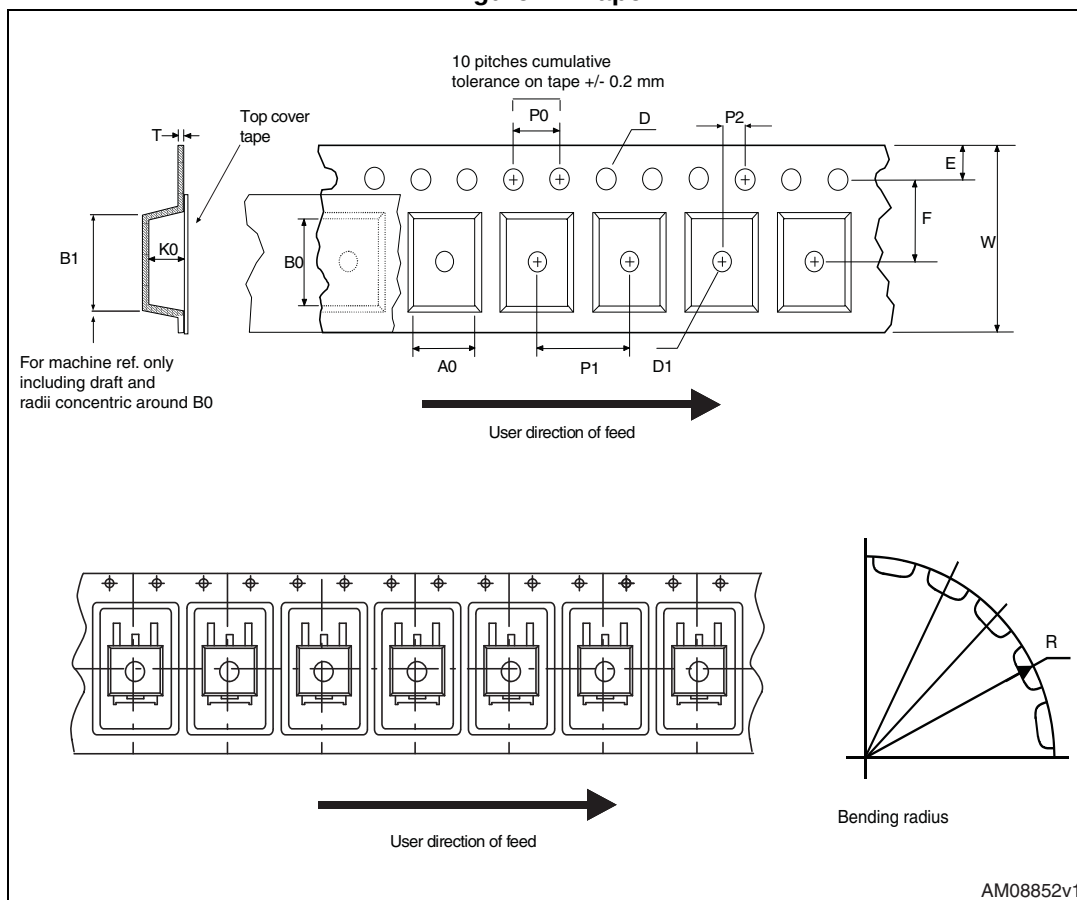
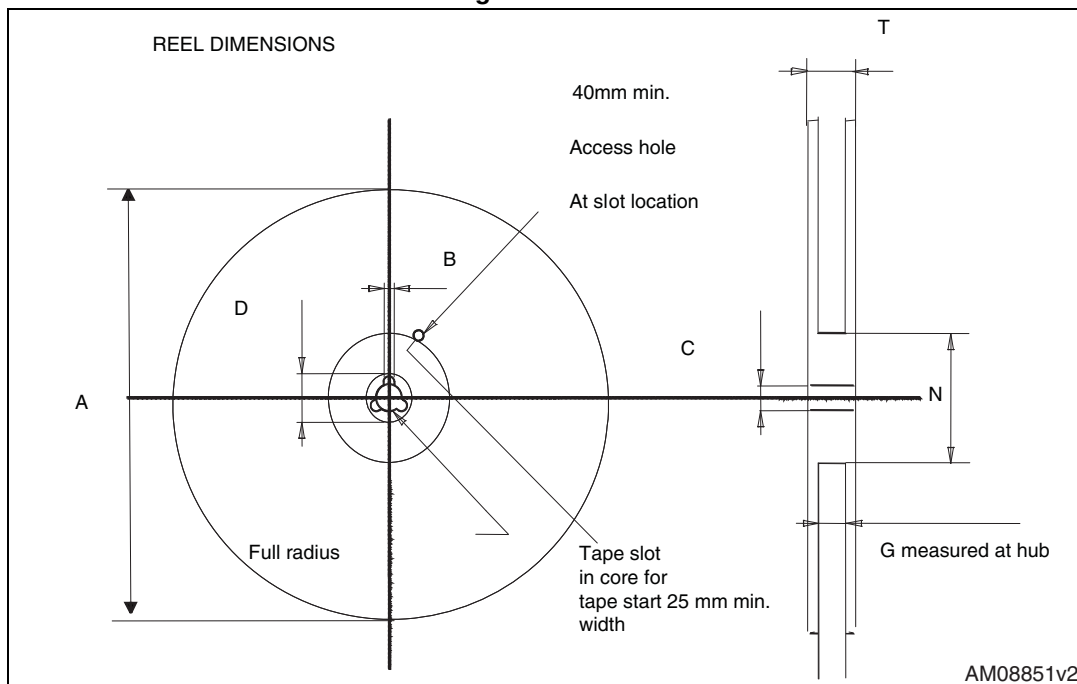


Figure 28. Reel



6 Revision history

Table 9. Document revision history

Date	Revision	Changes
26-Jul-2013	1	Initial release.
29-Jul-2013	2	Updated Table 3: Thermal data and added Figure 19: Safe operating area .
08-Oct-2013	3	Updated title, description and features in cover page.

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